

BTA10-600GP

10 A Triac

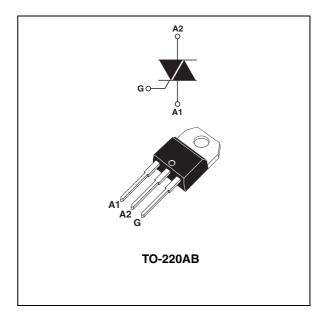
Features

- Low I_H:
 - 13 mA max
- High surge current:
 - I_{TSM} = 120 A
- I_{GT} specified in four quadrants
- Insulating voltage:
 - 2500 V_(RMS) (UL Recognized: E81734)

Description

The BTA10-600GP uses high performance, glass passivated chips.

The insulated TO-220AB package, the high surge current and low holding current make this product well adapted to CFL and LED dimmer applications.



1 Characteristics

Symbol	Parameter	Value	Unit		
V _{DRM} V _{RRM}	Repetitive peak off-state voltage $T_j = 125^{\circ} C$	600	V		
I _{T(RMS)}	RMS on-state current (360° conduction angle)	$T_c = 90^\circ C$	10	А	
	Non repetitive surge peak on-state current $(T_j \text{ initial} = 25^{\circ} \text{ C})$	t _p = 8.3 ms	126	А	
I _{TSM}		t _p = 10 ms	120	A	
l ² t	l^2 t Value for fusing $t_p = 10 \text{ ms}$		72	A ² s	
dl/dt	Critical rate of rise of on-state current $I_G = 500 \text{ mA} \text{ di}_G/\text{dt} = 1 \text{ A}/\mu\text{s}$	Repetitive F = 50 Hz	10	A/µs	
	$I_G = 500 \text{ mA}$ $u_{G'}u_{i} = 1 \text{ A}/\mu_{i}$	50			
T _{stg} T _j	Storage junction temperature range Operating junction temperature range		-40 to +150 -40 to +125	°C	

 Table 1.
 Absolute ratings (limiting values)

Table 2. Electrical characteristics

Test conditions		Quadrant		Value	Unit
$V_D = 12 V (DC)$ $R_L = 33 \Omega$	T – 25° C	- -	MAX	25	mA
	$T_j = 25^{\circ} C$	IV	MAX	100	
$V_{D} = 12 V (DC)$ $R_{L} = 33 \Omega$	$T_j = 25^\circ C$	I - II - III - IV	MAX	1.5	V
$V_D = V_{DRM}$ $R_L = 3.3 k\Omega$	T _j = 110° C	I - II - III - IV	MIN	0.2	V
$V_D = V_{DRM}$ I _G = 500 mA dI _G /dt = 3 A/µs	$T_j = 25^\circ C$	I - II - III - IV	TYP	2	μs
I _G = 1.2 I _{GT}	$T_j = 25^\circ C$	- -	TYP	20	mA
		IV		40	
I _T = 100 mA gate open	$T_j = 25^\circ C$		MAX	13	mA
I _{TM} = 14 A t _p = 380 μs	$T_j = 25^\circ C$		MAX	1.5	V
	$T_j = 25^\circ C$		MAX	0.01	mA
VDRM = VRRM	T _j = 110° C		MAX	0.5	ma
Linear slope up to $V_D = 67\% V_{DRM}$ gate open	T _j = 110° C		MIN	30	V/uo
			TYP	100	V/µs
(dl/dt)c = 2.2 A/ms	T 1100 C		MIN	1	M/up
	$r_j = 110^{-1}$ C		TYP	10	V/µs
	Test conditions $V_D = 12 V (DC)$ $R_L = 33 \Omega$ $V_D = 12 V (DC)$ $R_L = 33 \Omega$ $V_D = V_{DRM}$ $R_L = 3.3 k\Omega$ $V_D = V_{DRM}$ $I_G = 500 \text{ mA } dI_G/dt = 3 \text{ A/}\mu \text{s}$ $I_G = 1.2 I_{GT}$ $I_T = 100 \text{ mA } gate \text{ open}$ $I_{TM} = 14 \text{ A } t_p = 380 \ \mu \text{s}$ $V_{DRM} = V_{RRM}$ Linear slope up to $V_D = 67\% \ V_{DRM}$	$\label{eq:VD} \begin{array}{ c c c } \hline \mbox{Test conditions} \\ \hline V_D = 12 \ V \ (DC) & R_L = 33 \ \Omega & T_j = 25^\circ \ C \\ \hline V_D = 12 \ V \ (DC) & R_L = 33 \ \Omega & T_j = 25^\circ \ C \\ \hline V_D = \ V_{DRM} & R_L = \ 3.3 \ k\Omega & T_j = 110^\circ \ C \\ \hline V_D = \ V_{DRM} & I_G = 500 \ \text{mA} \ dI_G / dt = 3 \ A / \mu s & T_j = 25^\circ \ C \\ \hline I_G = 1.2 \ I_{GT} & T_j = 25^\circ \ C \\ \hline I_T = 100 \ \text{mA} \ gate \ open & T_j = 25^\circ \ C \\ \hline I_{TM} = 14 \ A \ t_p = 380 \ \mu s & T_j = 25^\circ \ C \\ \hline V_{DRM} = \ V_{RRM} & T_j = 25^\circ \ C \\ \hline I_{I} = 100^\circ \ C \\ \hline I_{I} = 100^\circ \ C \\ \hline I_{I} = 110^\circ \ C \\ \hline I_{I} = 10^\circ \ C \\ \hline I_{I} = 1$	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{ c c c c c } \hline \text{Test conditions} & \ & \ & \ & \ & \ & \ & \ & \ & \ & $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

1. For either polarity of electrode A_2 voltage with reference to electrode A_1 .



Symbol	Parameter	Value	Unit	
P _{G(AV)}	Average gate power dissipation		1	W
P _{GM}	Peak gate power dissipation	t _p = 20 μs	10	W
I _{GM}	Peak gate current	t _p = 20 μs	4	А
V _{GM}	Peak positive gate voltage	t _p = 20 μs	16	V

Table 3. Gate characteristics (maximum values)

Table 4.Thermal resistances

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	60	
R _{th(j-c)} DC	Junction to case for DC	4	° C/W
R _{th(j-c)} AC	Junction to case for 360° conduction angle (F = 50 Hz)	3	

Figure 1. Maximum rms power dissipation versus rms on-state current

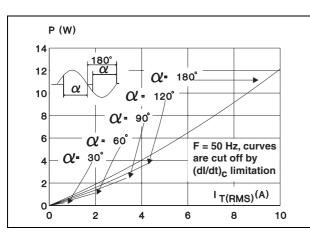
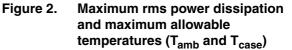
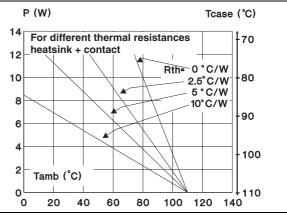
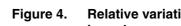


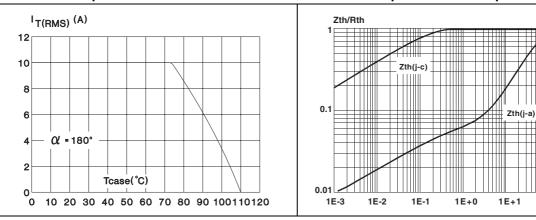
Figure 3. On-state rms current versus case temperature







Relative variation of thermal impedance versus pulse duration



tp(s)

1E+2 5E+2

Figure 5. Relative variation of gate trigger current and holding current versus junction temperature

Figure 6. Non repetitive surge peak on-state current versus number of cycles

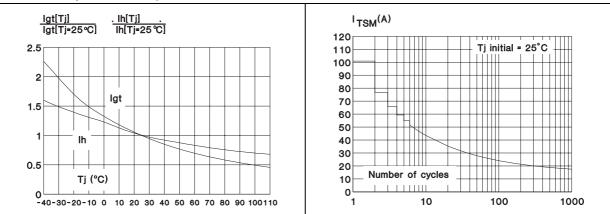
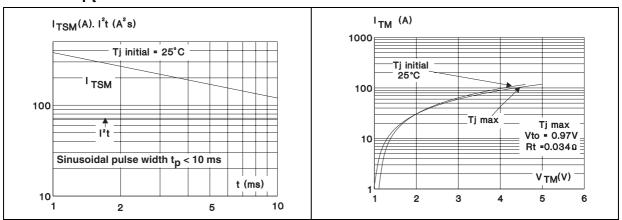


Figure 7. Non repetitive surge peak on-state Figure 8. current and corresponding value of I^2t

Ire 8. On-state characteristics (maximum values)





2 Package information

- Epoxy meets UL94,V0
- Cooling method: Conduction
- Recommended torque value: 0.4 to 0.6 N·m

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Table 5. TO-220AB dimensions

		Dimensions						
		Ref.	Mi	Millimeters		Inches		
			Min.	Тур.	Max.	Min.	Тур.	Max.
		А	15.20		15.90	0.598		0.625
		a1		3.75			0.147	
ØI	b2	a2	13.00		14.00	0.511		0.551
		В	10.00		10.40	0.393		0.409
	F	b1	0.61		0.88	0.024		0.034
A		b2	1.23		1.32	0.048		0.051
I4 I3 ·⊕··	c2 ↔	С	4.40		4.60	0.173		0.181
		c1	0.49		0.70	0.019		0.027
		c2	2.40		2.72	0.094		0.107
a2		е	2.40		2.70	0.094		0.106
		F	6.20		6.60	0.244		0.259
e b1	M	ØI	3.75		3.85	0.147		0.151
		14	15.80	16.40	16.80	0.622	0.646	0.661
		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		13	1.14		1.70	0.044		0.066
		М		2.60			0.102	



3 Ordering information

Table 6.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode	
BTA10-600GPRG	BTA10 600GP	TO-220AB	2.3 g	50	Tube	

4 Revision history

Table 7.Document revision history

Date	Revision	Changes
13-Sep-2011	1	Initial release



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